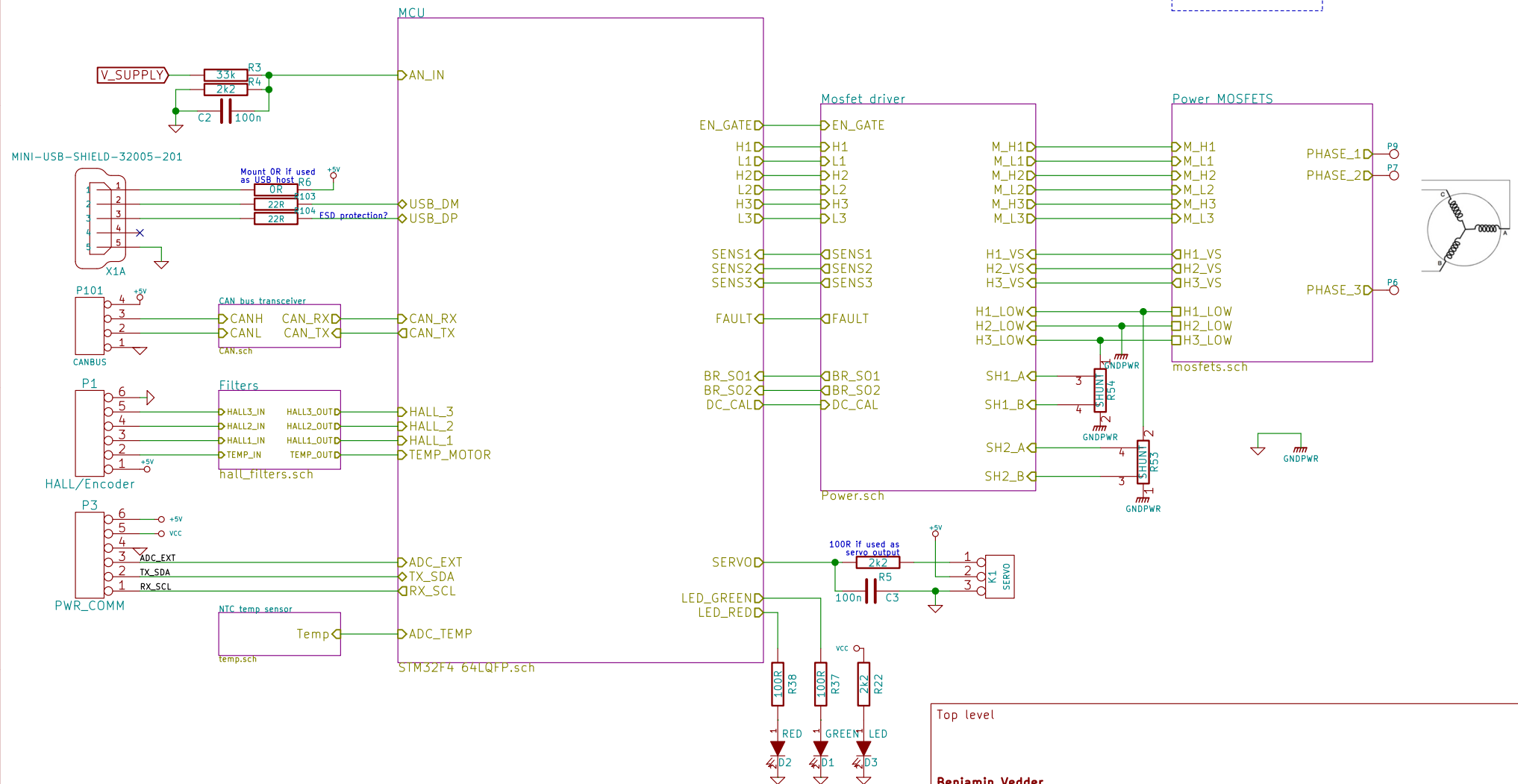


BLDC motor controller



Top level

Benjamin Vedder

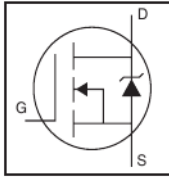
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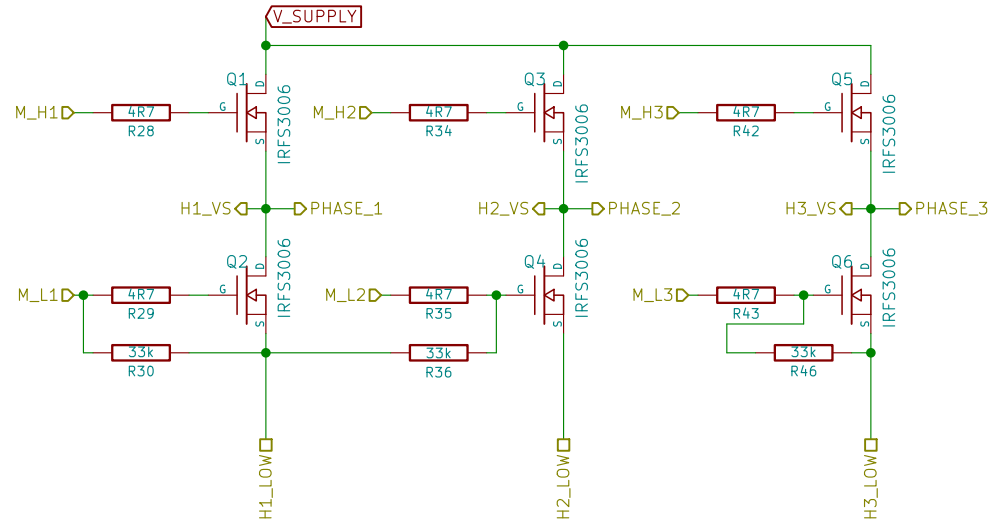
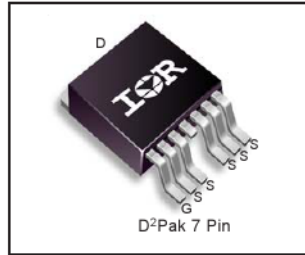
Size: A4 Date: 25 Aug 2014
KiCad E.D.A. kicad (2014-09-02 BZR 5112)-product

Rev: 4.6
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HEXFET® Power MOSFET



V_{DS}	60V
$R_{DS(on)}$ typ.	1.5m Ω
max.	2.1m Ω
I_D (Silicon Limited)	293A①
I_D (Package Limited)	240A



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{DS} = 10\text{V}$ (Silicon Limited)	293①	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{DS} = 10\text{V}$ (Silicon Limited)	207 ②	A
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{DS} = 10\text{V}$ (Package Limited)	240	A
I_{DW}	Pulsed Drain Current ③	1172	A
P_D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	375	W
	Linear Derating Factor	2.5	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery ④	11	V/ns
T_J	Operating Junction and Storage Temperature Range	-55 to +175	°C
T_{S10}	Soldering Temperature, for 10 seconds (1.6mm from case)	300	°C
	Mounting torque, 6-32 or M3 screw	10lb-in (1.1N-m)	

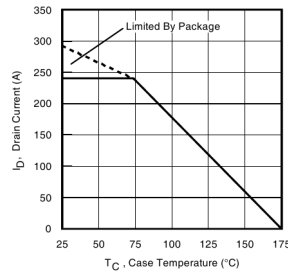


Fig 9. Maximum Drain Current vs. Case Temperature

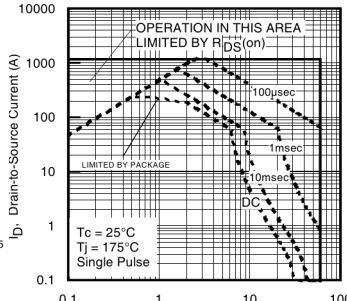
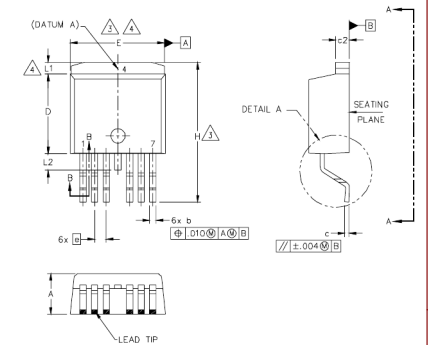


Fig 8. Maximum Safe Operating Area



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Sheet: /Power MOSFETS/

File: mosfets.sch

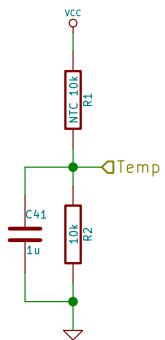
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Size: A4 Date: 25 Aug 2014

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Rev: 4.6

Id: 2/7



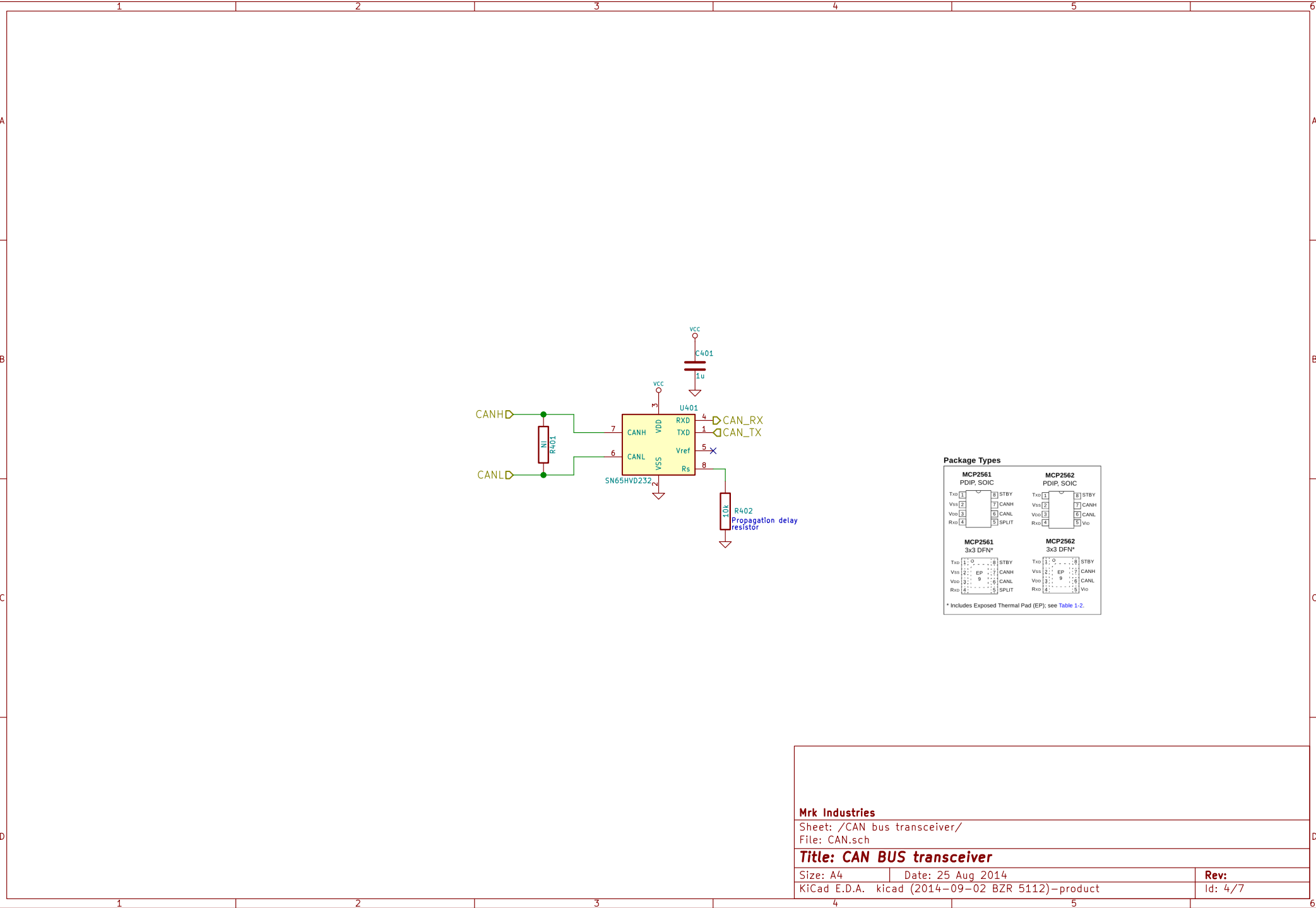
Mrk Industries

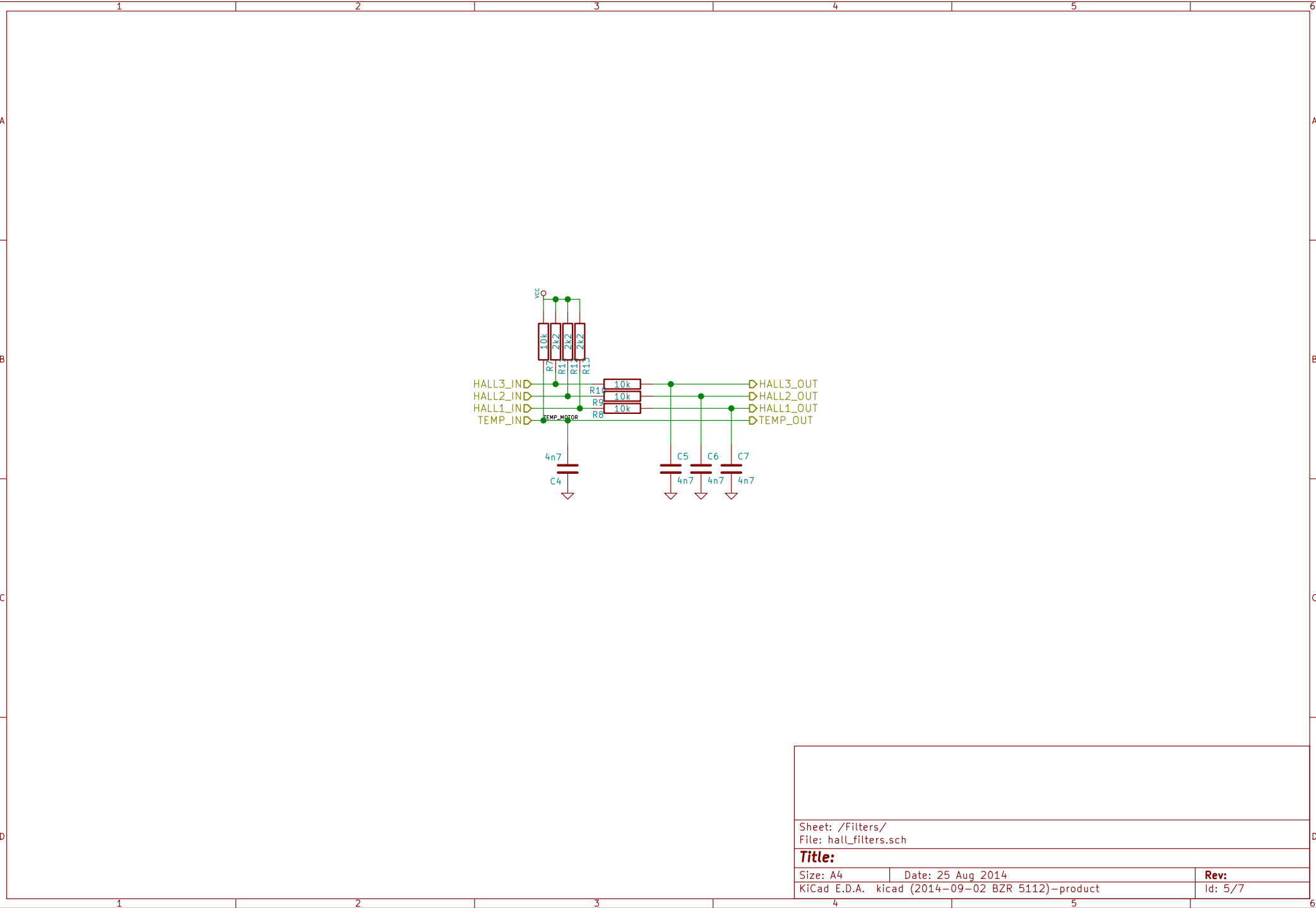
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File: temp.sch

Title: NTC resistor temperature sensor

Size: A4 Date: 27 sep 2014
KiCad E.D.A. kicad (2014-09-02 BZR 5112)-product

Rev:
Id: 3/7





Sheet: /Filters/ File: hall_filters.sch		
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Size: A4	Date: 25 Aug 2014	Rev:
KiCad E.D.A. kicad (2014-09-02 BZR 5112)-product		Id: 5/7

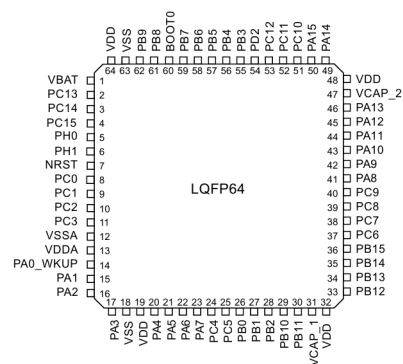
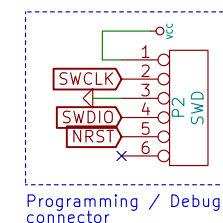


VCC

2.2u C10 2.2u C11 2.2u C12 2.2u C13 2.2u C14

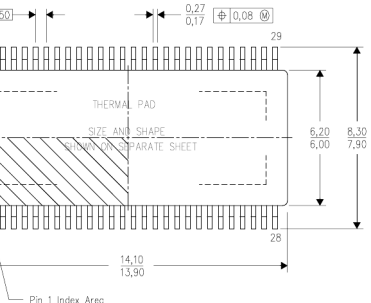
GND

Bypass, place next to VDD pins



Rev: 4.6
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- Operating Supply Voltage 8V–60V
- 2.3A Sink and 1.7A Source Gate Drive Current Capability
- Integrated Dual Shunt Current Amplifiers With Adjustable Gain and Offset
- Integrated Buck Converter to Support up to 1.5A External Load
- Independent Control of 3 or 6 PWM Inputs
- Bootstrap Gate Driver With 100% Duty Cycle Support
- Programmable Dead Time to Protect External FETs from Shoot Through
- Programmable Overcurrent Protection of External MOSFETs
- Thermally Enhanced 56-Pin TSSOP Pad Down DCA Package



			MIN	TYP	MAX	UNITS
PVDD1	DC supply voltage PVDD1 for normal operation	Relative to PGND		8	60	V
PVDD2	DC supply voltage PVDD2 for buck converter		3.5	60	V	
C _{AVDD}	External capacitance on AVDD pin (ceramic cap)	20% tolerance		1		μF
C _{VDVDD}	External capacitance on VDDV pin (ceramic cap)	20% tolerance		1		μF
C _{VDVDD}	External capacitance on VDDV pin (ceramic cap)	20% tolerance		2.2		μF
C _{CP1}	Flying cap on charge pump pins (between CP1 and CP2)	(ceramic cap) 20% tolerance		22		nF
C _{CP2}	Bootstrap cap (ceramic cap)			100		nF
EN_IN	Input current of digital pins when EN_GATE is high			1	100	μA
EN_IN	Input current of digital pins when EN_GATE is low			1	10	μA
C _{IN}	Maximum capacitance on digital input pin			1		μF
C _{IO_OPA}	Maximum output capacitance on outputs of shunt amplifier			20		pF
R _{OTC}	Dead time control resistor range. Time range is 50ns (-GND) to 500ks (150KΩ) with a linear approximation.		0	150		kΩ
I _{FAULT}	FAULT pin sink current. Open-drain	V = 0.4 V		2		mA
I _{OUTW}	OUTW pin sink current. Open-drain	V = 0.4 V		2		mA
V _{REF}	External voltage reference voltage for current shunt amplifiers		2	6		V
f _{SW}	Operating switching frequency of gate driver	C _{g(TOT)} = 25 nC or total 30 mA gate drive average current			200	kHz
T _A	Ambient temperature		-40	125		°C

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